Product Overview

FFSH10120A-F085: SiC Schottky Diode 1200 V, 10 A

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175 °C
- AEC-Q101 qualified and PPAP Capable
- No Reverse Recovery / No Forward Recovery
- High Surge Current Capacity
- Ease of Paralleling
- Positive Temperature Coefficient

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

End Products

- Automotive HEV-EV Onboard Chargers

Part Electrical Specifications

Product	Compliance	Status	Device Grade	Configuration	V_{RRM} (V)	$I_{F(ave)}$ (A)	V_F (Max)	I_{FSM} (A)	I_R (Max) (µA)	Package Type
FFSH10120A-F085	AEC Qualified PPAP Capable Pb-free Halide free	Active		with Schottky Diode	1200	10	1.75	90	200	TO-247-2

For more information please contact your local sales support at www.onsemi.com.

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